

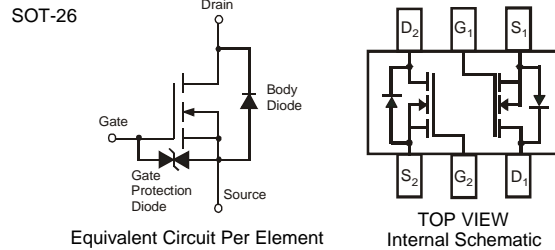
## Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **ESD Protected Up To 2kV**
- **"Green" Device (Note 4)**



## Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.015 grams (approximate)



## Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current (Note 1)	Continuous Pulsed (Note 3)	$I_D$	305
			800

## Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	$P_d$	225	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_j, T_{STG}$	-65 to +150	$^\circ\text{C}$

## Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 5)</b>						
Drain-Source Breakdown Voltage	$BV_{DS}$	60	—	—	V	$V_{GS} = 0V, I_D = 10\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 20V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 5)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	1.6	2.5	V	$V_{DS} = 10V, I_D = 1\text{mA}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	2.4	$\Omega$	$V_{GS} = 10V, I_D = 200\text{mA}$
		—	—	4.0		$V_{GS} = 4V, I_D = 200\text{mA}$
Forward Transfer Admittance	$ Y_{fs} $	100	—	—	ms	$V_{DS} = 10V, I_D = 200\text{mA}$
Diode Forward Voltage (Note 5)	$V_{SD}$	0.5	—	1.4	V	$V_{GS} = 0V, I_S = 115\text{mA}$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{iss}$	—	—	50	pF	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	—	25	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	—	5.0	pF	

- Notes:
1. Device mounted on FR-4 PCB.
  2. No purposefully added lead.
  3. Pulse width  $\leq 10\mu\text{s}$ , Duty Cycle  $\leq 1\%$ .
  4. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  5. Short duration pulse test used to minimize self-heating effect.

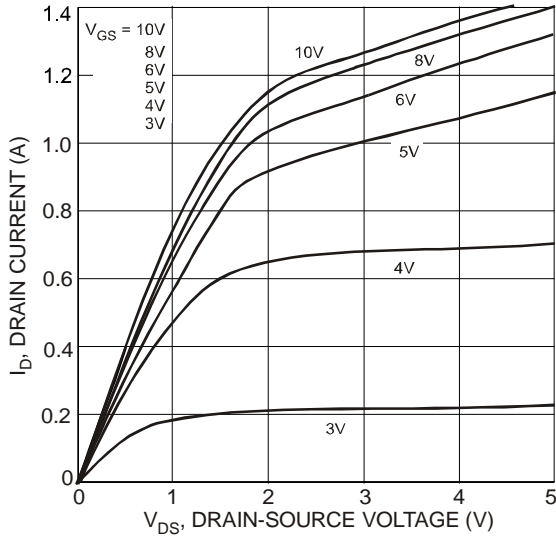


Fig. 1 Typical Output Characteristics

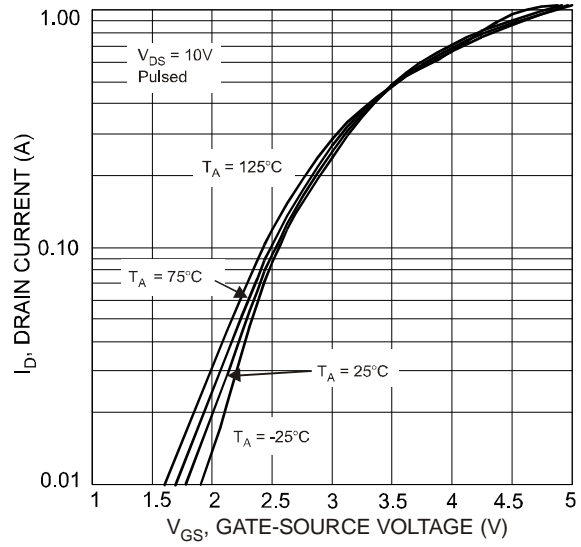


Fig. 2 Typical Transfer Characteristics

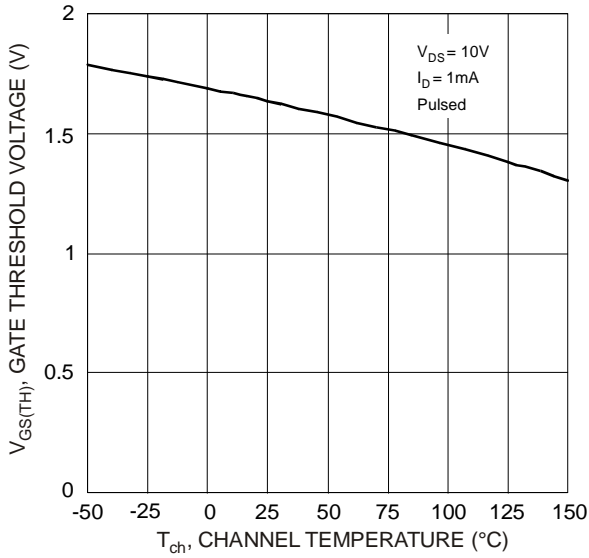


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

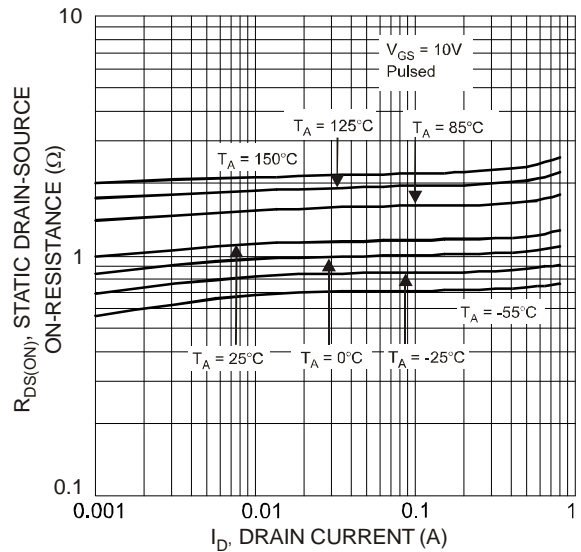


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

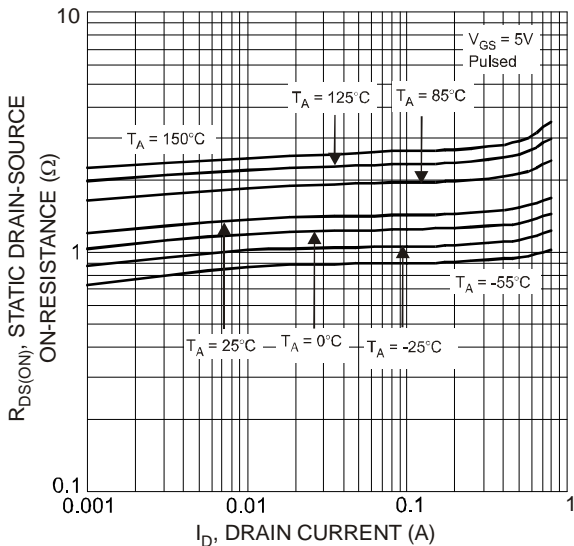


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

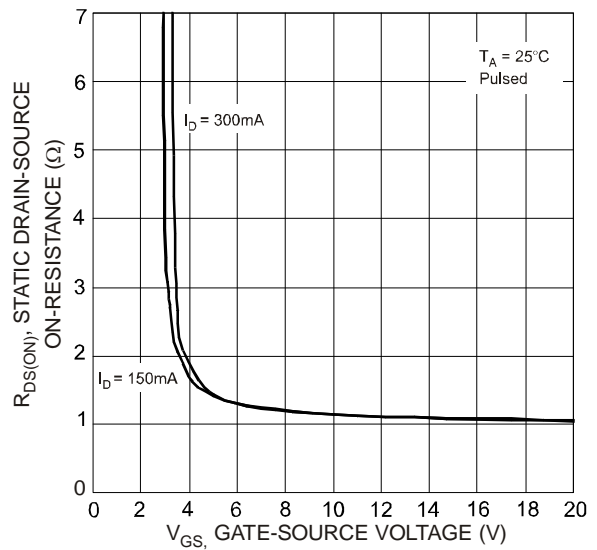


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

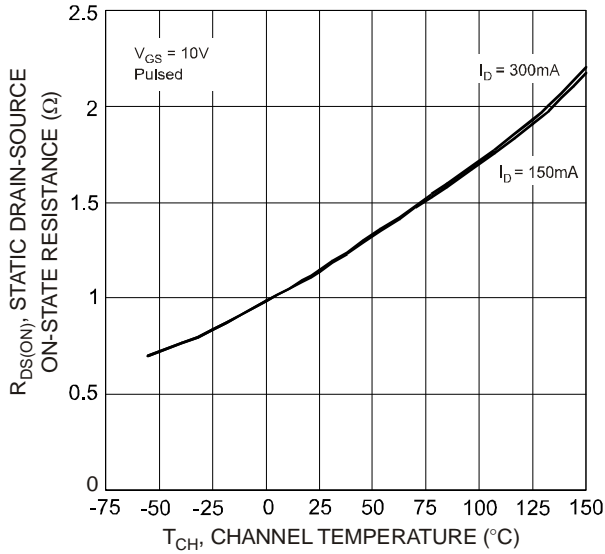


Fig. 7 Static Drain-Source On-State Resistance vs. Channel Temperature

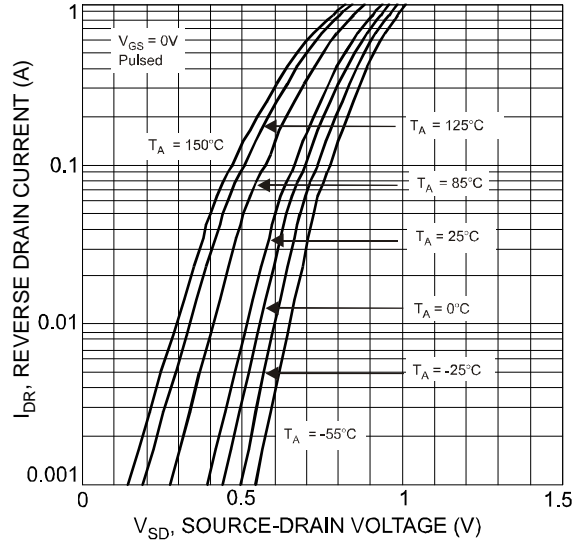


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

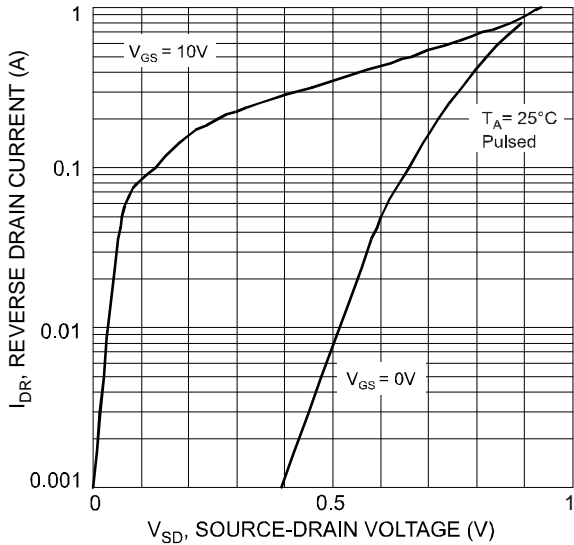


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

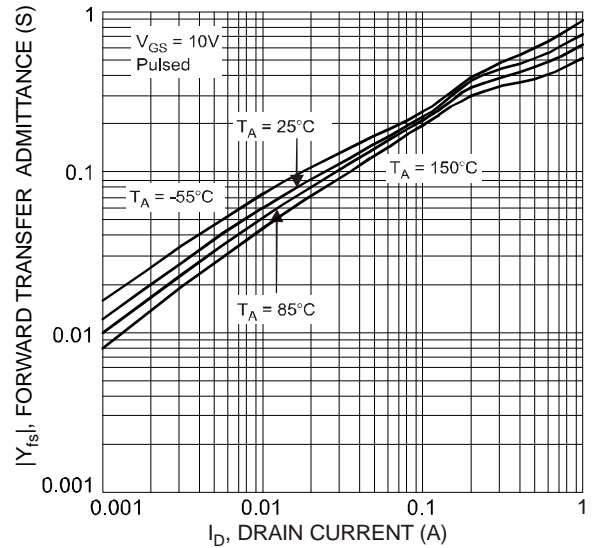


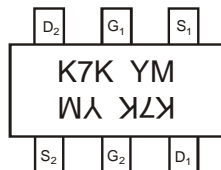
Fig. 10 Forward Transfer Admittance vs. Drain Current

**Ordering Information** (Note 6)

Part Number	Case	Packaging
DMN601DMK-7	SOT-26	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**



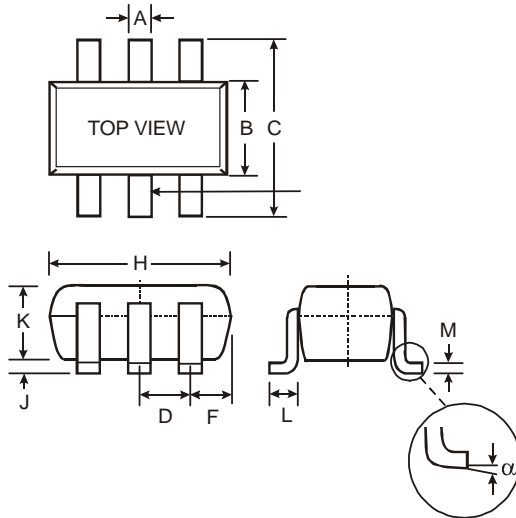
K7K = Marking Code  
YM = Date Code Marking  
Y = Year ex: S = 2005  
M = Month ex: 9 = September

Date Code Key

Year	2005	2006	2007	2008	2009	2010	2011	2012
Code	S	T	U	V	W	X	Y	Z

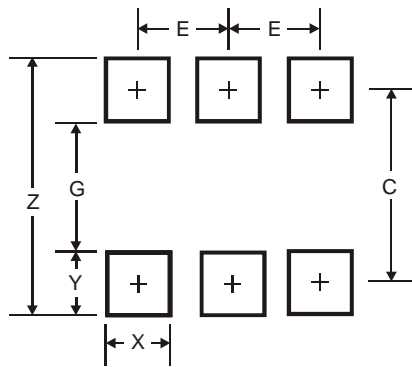
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Package Outline Dimensions**



SOT-26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
F	—	—	0.55
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C	2.40
E	0.95

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